

SOT-23 Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

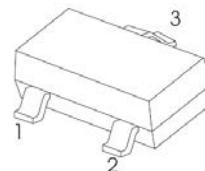
- LOW $V_{CE(sat)}$
- Excellent DC current gain characteristics. Power dissipation

MAXIMUM RATINGS* $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-20	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-2	A
P_C	Collector Power Dissipation	350	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^\circ\text{C}$

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}$, $I_E = 0$	-20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}$, $I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20\text{V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2\text{V}$, $I_C = -0.1\text{A}$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}$, $I_B = -0.1\text{A}$			-0.5	V
Transition frequency	f_T	$V_{CE} = -2\text{V}$, $I_C = -0.5\text{A}$, $f = 100\text{MHz}$		240		MHz

CLASSIFICATION OF h_{FE}

Rank	Q	R
Range	120-270	180-390
Marking	AEQ	AER

Typical Characteristics

